Spin-resolved Visible Optical Spectra and Electronic Characteristics of Defect-mediated Hexagonal Boron Nitride Monolayer

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ABSTRACT
The defect-mediated hexagonal boron nitride (hBN) supercell display the visible optical spectra and electronic characteristics. The defects in the hBN supercell include the atomic vacancy, antisite, antisite vacancy, and substitution of a foreign atom for boron or nitrogen. The hBN supercell with VB, CB, and NB-VN has the high electron density of states across the Fermi level which indicates the high conductive electronic characteristics. The hBN with defects including atomic vacancy, antisite vacancy, and substitution of a foreign atom for boron or nitride exhibit the distinct spin-resolved optical and electronics characteristics, while the defects of boron and nitrogen antisite do not display the spin-resolved optical characteristics. The hBN with positively charged defects has a dominant optical and electronic characteristics at the longer spectral region.

I. INTRODUCTION
Boron nitride (BN) has the unique electronic, chemical, and materials properties including wide electronic bandgap, strong covalent bonding, and high melting point.1–5 The BN crystal has three different structures of hexagonal BN (hBN), cubic BN (cBN), and wurzite BN (wBN). Among these structures, hBN atomic layer is chemically stable at room temperature with ambient pressure. In analogy to graphite, the hBN has a strong covalence bonding within a layer with a honeycomb atomic structure, and a weak van der Waals force between layers. In contrast to the semi-metallic graphite, the hBN has a wide band gap in the ultraviolet (UV) spectral region.6–10

The hBN monolayer also has relatively wide bandgap compared to the other two-dimension (2D) materials.11–13 The wide bandgap of hBN atomic layer is easy to host the optically
active defects that introduce the ground and excited states within the forbidden band.\textsuperscript{14-17} Single photon emission has been also demonstrated with atomic defects in the hBN atomic layers.\textsuperscript{17-20} The theoretical modeling and calculation of the electronic, mechanical, thermal and optical properties in defects mediated hBN were also reported.\textsuperscript{21-32} Various defects of atomic vacancy,\textsuperscript{21-28} atomic substitution,\textsuperscript{25-29} Stone-Wales defects\textsuperscript{30,31} and large hole in the atomic layer\textsuperscript{32} have been explicitly investigated. In this article, the spin-resolved electronic and optical properties of hBN monolayer with various local defects were analyzed with the first principle calculation with the density functional theory to explore the optical transitions in visible spectral region. The local point defects in hBN monolayer include the vacancy of boron or nitrogen, antisite nitrogen or boron, antisite nitrogen or boron vacancy, and substation of carbon to the boron or nitrogen site. The studies of spin-resolved electronic and optical characteristics of hBN monolayer with various defects will considerably promote the proposed quantum optical application.

II. METHODOLOGY
The Virtual Nanolab Atomistix ToolKit (ATK) package with the density functional theory (DFT) was used for the first principle calculation of the electronic and optical properties of BN monolayer for the various point defects.\textsuperscript{33} The Perdew-Burke-Ernzerhof (PBE) parametrization of generalized gradient approximations (GGA) exchange correlation with a double zeta polarized (DZP) basis was used with a mesh cut-off energy of 150 Ry.\textsuperscript{34} The electron temperature was set to 300 K for the simulations of the band structure, density of states (DOS), and dielectric constant (ε) for the defects in BN monolayer. 11×11×1 Monkhorst-Pack k-grid mesh in this simulation was employed.\textsuperscript{35} All atomic positions and lattice constants were optimized by using the generalized gradient approximations (GGA) with the maximum Hellmann-Feynman forces of 0.05 eV/Å, which was sufficient to obtain the relaxed structures.\textsuperscript{36} The Pulay-mixer algorithm was employed as an iteration control parameter with a tolerance value of 10\textsuperscript{5}.\textsuperscript{37} The maximum number of fully self-consistent field (SCF) iteration steps was set to 100.\textsuperscript{38} The periodic boundary conditions were employed for all the three directions.\textsuperscript{39} A separation of 60 Å for the adjacent layers was utilized to minimize the mirroring interaction. The self-consistent field calculations fully guaranteed the convergence within the iteration steps.
The hBN supercell consists of 4×4 unit cells with 16 boron atoms and 16 nitrogen atoms. Figure 1 shows the defects in a supercell including the boron vacancy (V_B), nitrogen vacancy (V_N), substitution of boron for nitrogen (B_N), substitution of nitrogen for boron (N_B), substitution of carbon for boron (C_B), substitution of carbon for nitrogen (C_N), substitution of boron for nitrogen with boron vacancy (B_N-V_B), substitution of nitrogen for boron with nitrogen vacancy (N_B-V_N). The electronic band structure, density of states (DOS), and dielectric constant (ε) of hBN supercell with various defects were characterized with the first principle calculation with density functional theory. The first principle calculation for electronic and optical properties of BN monolayer with atomic defects included the spin-orbit coupling (SOC). The spin-resolved absorption and reflection coefficients were calculated as a function of photon energy [supplementary information]. Also, the formation energy of hBN for various defect studied to analysis the stability of each structure.

**III. RESULTS AND DISCUSSION**
Figure 2 displayed the spin-resolved electronic band structure of hBN monolayer with various defects. The energy levels were introduced within the forbidden band between conduction band minimum (CBM) and valence band maximum (VBM). The electronic band structure of pristine BN monolayer displayed a direct bandgap ~4.7 eV which were located at K-point in the first Brillouin Zone. The energy levels of electron spin-up and -down states for hBN with various defects were clearly resolved except the hBN with B_N defect where the energy levels were degenerated. The Fermi energy level which was pinned to 0 eV was fluctuated between the CBM and the VBM of atomic layer with various defects. The atomic layer with V_B defect displayed the hole-dominant characteristics due to the ascendant uncoupled-holes around the boron vacancy,\textsuperscript{14} while the atomic layer with V_N defect exhibited a donor-dominant characteristics due to the ascendant uncoupled-electrons around the nitrogen vacancy.
Fig. 3. Spin-resolved electronic density of states (DOS) of hBN monolayer with various defects of (a) $V_B$; (b) $V_N$; (c) $B_N$; (d) $N_B$; (e) $C_B$; (f) $C_N$; (g) $B_N$-$V_B$; (h) $N_B$-$V_N$. The vertical dotted lines indicate the Fermi energy level which is pinned to 0 eV. The red and blue lines indicate the spin-up and -down DOS.

The figure 3 shows the spin-resolved electronic density of states (DOS) for the hBN monolayer with various defects. The vertical dash line indicates the Fermi energy level which is pinned to 0 eV. The abundant electronic DOS across the Fermi level were observed for the BN atomic layer with $V_B$, $C_B$, and $N_B$-$V_N$ defects which indicates the high conductive electronic characteristics. For the BN atomic layer with $B_N$ defect, the spin up- and spin down-DOS were overlapped each other which led to the zero spin-dipole magnetic-moment. The atomic layer with defects of $V_N$ and $B_N$-$V_B$ displayed a similar electronic band structure and DOS due to the structure instability with $B_N$-$V_B$ defect where the boron substitution jumped to the neighboring vacancy position. The atomic layer with $B_N$-$V_B$ defect eventually transformed into the atomic layer with $V_N$-like defect during the structural optimization process which is described in the supplementary Information. The $B_N$-$V_B$ defect is unstable in the structure because the stable structure has a minimum total energy of system.
Figure 4 shows the spin-resolved and -unresolved absorption spectra of hBN with various defects in hBN supercell. The absorption peaks of hBN with defects was shifted in the visible spectral region. The absorption peak of spin-unresolved hBN with C\textsubscript{N} was shown at \(~1.75\) eV (figure 4 (f)), while that with N\textsubscript{B} defect was exhibited at \(~2.8\) eV (figure 4(d)). The hBN with N\textsubscript{B}-V\textsubscript{N} defect displayed the anisotropic optical properties of distinct absorption and reflection coefficient along the zigzag and armchair directions as shown in figure 4(h) and 4(i), respectively. The hBN with N\textsubscript{B}-V\textsubscript{N} defect exhibited an unresolved absorption peaks at \(~1.96\) eV along the zigzag direction, and \(~3.01\) eV and \(~3.34\) eV along the armchair direction. The spin-resolved absorption coefficient revealed that the spin-up electron has the higher absorption coefficient than the spin-down electrons for the atomic layer with V\textsubscript{B}, V\textsubscript{N}, C\textsubscript{B}, are B\textsubscript{N}-V\textsubscript{B} defects, while the spin-up and spin-down electrons have almost equal absorption peak for the atomic layers with B\textsubscript{N} and N\textsubscript{B} defects. The spin-down electrons in atomic layer with C\textsubscript{N} defect displayed the dominant absorption at \(~1.75\) eV.
Fig. 5. Reflection spectra of the various defects in hBN supercell. The black, red, and blue lines indicate the spin-unresolved (x10), -up, and -down reflection spectra.

Figure 5 shows the reflection coefficients as a function of photon energy for the hBN monolayer with different defects. The spin-resolved reflection coefficients of hBN atomic layer with defects was one-order larger than that of spin-unresolved electrons because the real part ($\varepsilon'_r$) of dielectric constant for spin-resolved hBN atomic layer with defects is larger than that of spin-unresolved hBN atomic layer with defects. The additional information of dielectric constant and mathematical formula can be found in the table 1s and section II of supplementary information. The hBN with C_N defect has the highest reflection peak at ~6.0 eV whereas the hBN with V_B defect has the lowest peak at ~5.8 eV. It should be noteworthy that hBN with defect V_B has the two prominent reflection peaks at ~1.89 eV and ~2.10 eV. The hBN atomic layer with defects has minimal reflection coefficients from ~4.0 to 5.0 eV, which imply the existence of optical absorption through optical bandgap. In analogy to the absorption spectra, the reflection spectra of hBN with B_N and N_B defects were overlapped with degeneracy for the spin-up and –down electrons.
Fig. 6. Optical spectra of hBN monolayer with charged defects. (a) absorption and (b) reflection spectra of hBN supercell with various charged defects of $V_{B}^{-1}$, $V_{B}^{-2}$, and $V_{B}^{-3}$ (c) absorption and (d) reflection spectra of hBN supercell with various charged defects of $V_{N}^{+1}$, $V_{N}^{+2}$, and $V_{N}^{+3}$.

The charged point defect also modified the optical spectra of hBN monolayer. The $V_{B}$ is an acceptor-like defect because the Fermi level shifted toward the VBM. The $V_{N}$ is a donor-like defect because the Fermi level shifted toward the CBM. Therefore, the $V_{B}$ defect has an affinity with the negative charge of electron, and the $V_{N}$ defect has an affinity with the positive change of hole. Figure 6 displays the absorption and reflection coefficients of hBN atomic layer with the charged defects of $V_{B}$ for $V_{B}^{-1}$, $V_{B}^{-2}$, and $V_{B}^{-3}$ and $V_{N}$ for $V_{N}^{+1}$, $V_{N}^{+2}$, and $V_{N}^{+3}$. The hBN with positively charged defects has a dominant optical and electronic characteristics at the longer spectral region. The hBN with negatively charged defects of $V_{B}^{-1}$ and $V_{B}^{-2}$ have visible optical characteristics in visible spectral region, but that with $V_{B}^{-3}$ does not display the visible optical characteristics.

IV. CONCLUSION

In summary, the first-principle calculations with density functional theory characterized the visible optical spectra of hBN monolayer with various point defects. The hBN supercell with $V_{B}$, $C_{B}$, and $N_{B}$-$V_{N}$ exhibits the high electron density of states across the Fermi level which indicates the high conductive electronic characteristics. The hBN atomic layer with $N_{B}$-$V_{N}$ defects displayed the
anisotropic optical and electronic characteristics along the armchair and zigzag directions. The hBN atomic layer with defects, except for the antisite of boron and nitrogen, displayed the spin-resolved optical absorption within the forbidden gap. The hBN with positively charged defects has a dominant optical and electronic characteristics at the longer spectral region. Therefore, the spin-resolved visible optical and electronic characteristics of defect-mediated hBN atomic layers will promote the exploitation of 2D optoelectronics.

SUPPLEMENTARY MATERIAL
See supplementary material for the detailed information regarding formulation and insights into absorption and reflection coefficients of spin resolved and unresolved electrons, the dielectric constant, the structural optimization and stability.

CONFLICTS OF INTERETS
The authors declare no competing financial interests.

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